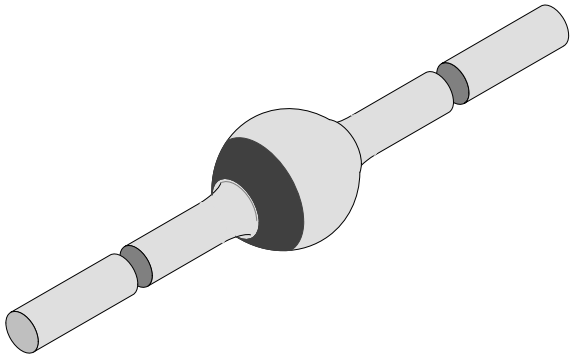
Very Fast Soft–Recovery Avalanche Rectifier

Features

- Glass passivated
- Hermetically sealed package
- Very low switching losses
- Low reverse current
- High reverse voltage



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Applications

Switched mode power supplies
High–frequency inverter circuits

Absolute Maximum Ratings

T_j = 25°C

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage =Repetitive peak reverse voltage		BYM36A	V_R =V_{RRM}	200	V
		BYM36B		400	V
		BYM36C		600	V
		BYM36D		800	V
		BYM36E		1000	V
Peak forward surge current	t_p=10ms, half sinewave		I_{FSM}	65	A
Average forward current		BYM36A –BYM36C	I_{FAV}	3	A
		BYM36D –BYM36E	I_{FAV}	2.9	A
Non repetitive reverse avalanche energy	$I_{(BR)R}$=400mA, inductive load		E_R	10	mJ
Junction and storage temperature range			T_j=T_{stg}	–55...+175	˚C

Maximum Thermal Resistance

T_j = 25°C

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	l=10mm, T_L=constant	R_{thJA}	25	K/W
	on PC Board with spacing 37.5 mm	R_{thJA}	70	K/W

Electrical Characteristics

T_j = 25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=3A	BYM36A –BYM36C	V_F			1.6	V
		BYM36D –BYM36E	V_F			1.78	V
	I_F=3A, T_j=175°C	BYM36A –BYM36C	V_F			1.22	V
		BYM36D –BYM36E	V_F			1.28	V
Reverse current	V_R=V_{RRM}		I_R			5	µA
	V_R=V_{RRM}, T_j=150°C		I_R			100	µA
Reverse breakdown voltage	I_R=100µA	BYM36A	$V_{(BR)R}$	300			V
		BYM36B	$V_{(BR)R}$	500			V
		BYM36C	$V_{(BR)R}$	700			V
		BYM36D	$V_{(BR)R}$	900			V
		BYM36E	$V_{(BR)R}$	1100			V
Reverse recovery time	I_F=0.5A, I_R=1A, i_R=0.25A	BYM36A –BYM36C	t_{rr}			100	ns
		BYM36D –BYM36E	t_{rr}			150	ns

Characteristics (T_j = 25°C unless otherwise specified)

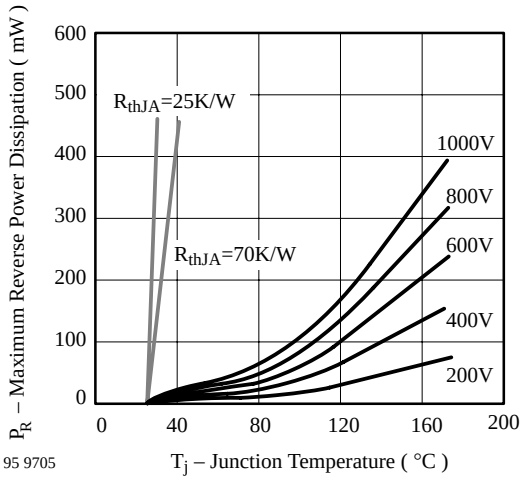


Figure 1. Max. Reverse Power Dissipation vs. Junction Temperature

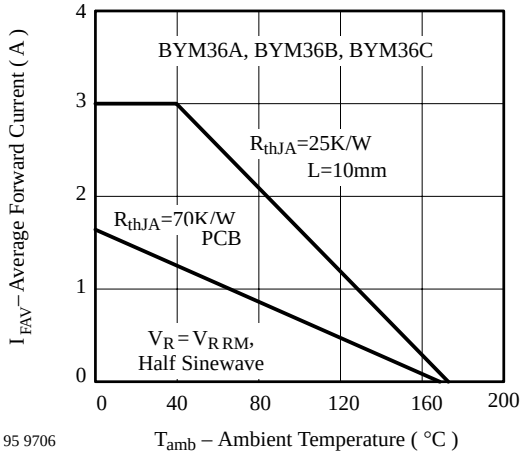


Figure 2. Max. Average Forward Current vs. Ambient Temperature

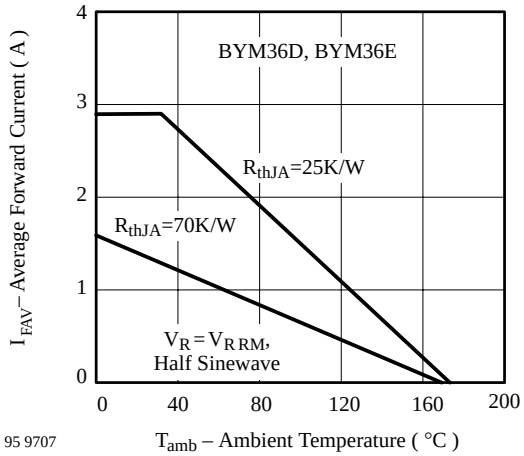


Figure 3. Max. Average Forward Current vs. Ambient Temperature

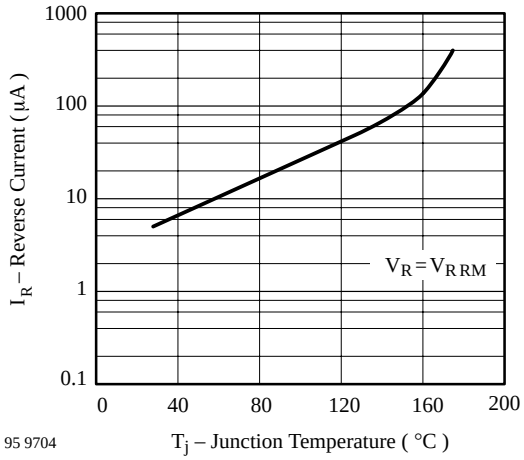


Figure 4. Max. Reverse Current vs. Junction Temperature

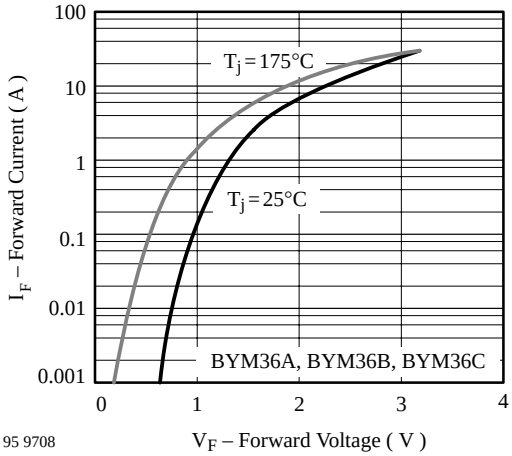


Figure 5. Max. Forward Current vs. Forward Voltage

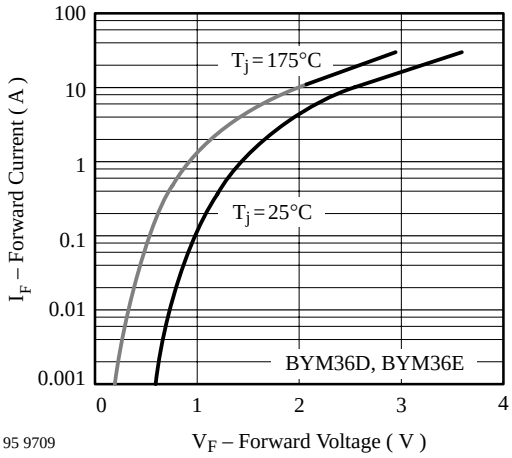
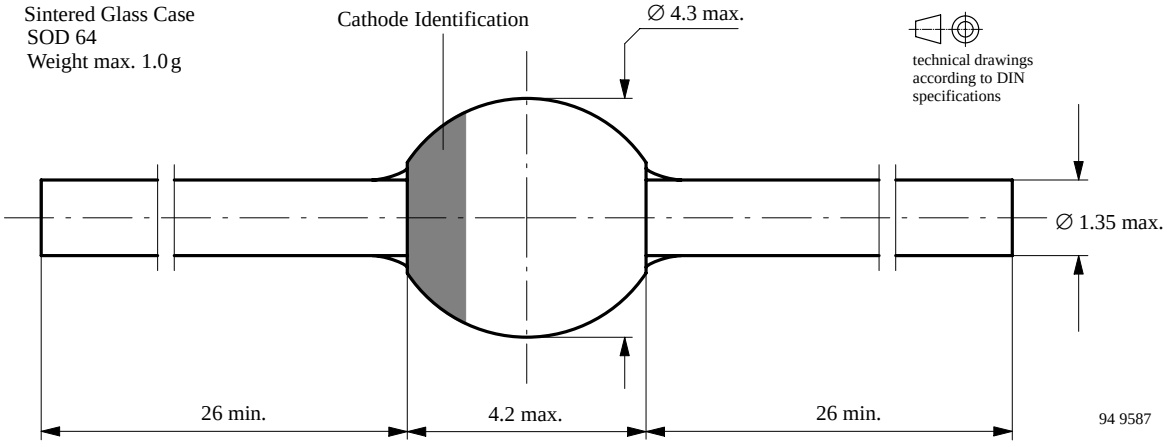


Figure 6. Max. Forward Current vs. Forward Voltage

Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.

2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems
   with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively

2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA

3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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